

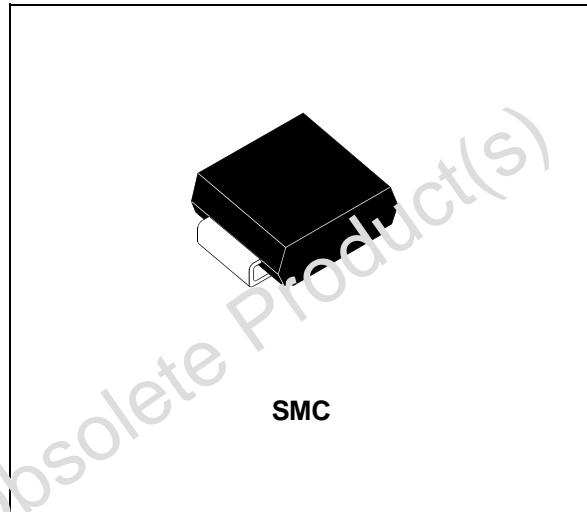
FAST RECOVERY RECTIFIER DIODES

FEATURES

- VERY LOW REVERSE RECOVERY TIME
- VERY LOW SWITCHING LOSSES
- LOW NOISE TURN-OFF SWITCHING
- SURFACE MOUNT DEVICE

DESCRIPTION

Single high voltage rectifier ranging from 200V to 400 V suited for Switch Mode Power Supplies and other power converters.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$I_{F(RMS)}$	RMS forward current	10	A
$I_{F(AV)}$	Average forward current	3	A
I_{FSM}	Non repetitive surge peak forward current	60	A
$T_{stg}\text{ }/\text{ }T_j$	Storage and junction temperature range	- 40 to + 150	°C

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive peak reverse voltage	400	V

THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
$R_{th} (j-l)$	Junction-leads	20	°C/W

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ELECTRICAL CHARACTERISTICS STATIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
V_F *	$T_j = 25^\circ C$	$I_F = 3 A$			1.5	V
	$T_j = 100^\circ C$			1.05	1.4	
I_R **	$T_j = 25^\circ C$	$V_R = V_{RRM}$			10	μA
	$T_j = 100^\circ C$			0.2	0.6	mA

Pulse test : * $t_p = 380 \mu s$, duty cycle < 2 %

** $t_p = 5 ms$, duty cycle < 2 %

RECOVERY CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
t_{rr}	$T_j = 25^\circ C$	$I_F = 0.5A$	$I_{rr} = 0.25A$		25	ns
		$I_F = 1A$	$dI_F/dt = -15A/\mu s$		60	
		$V_R = 30V$				

TURN-OFF SWITCHING CHARACTERISTICS (Without serie inductance)

Symbol	Test Conditions		Min.	Typ.	Max.	Unit	
t_{IRM}	$V_{CC} = 200V$	$I_F = 3A$	$L_p \leq 0.05\mu H$		35	50	ns
I_{RM}		$T_j = 100^\circ C$	$dI_F/dt = -50A/\mu s$		1.5	2	

To evaluate the conduction losses use the following equation :

$$P = 1.1 \times I_F(AV) + 0.08 \times I_F^2(RMS)$$

Voltage (V)	200	300	400
Marking	C2	C3	C4

Laser marking
Logo indicates cathode

Fig.1 : Low frequency power losses versus average current.

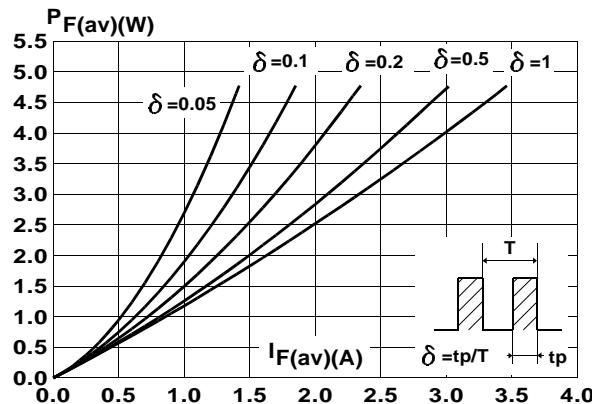


Fig.3 : Non repetitive surge peak forward current versus overload duration.

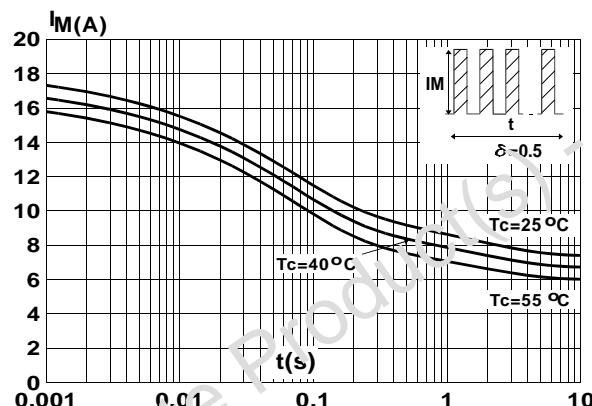


Fig.5 : Voltage drop versus forward current. (Maximum values)

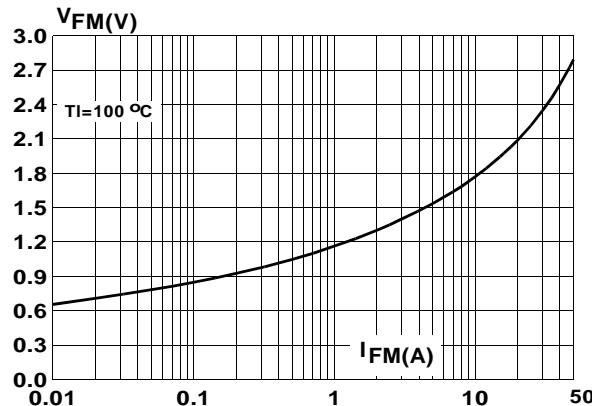


Fig.2 : Peak current versus form factor.

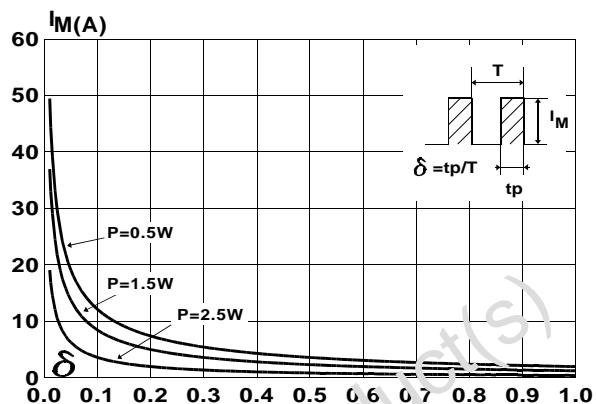


Fig.4 : Relative variation of thermal impedance junction to lead versus pulse duration.

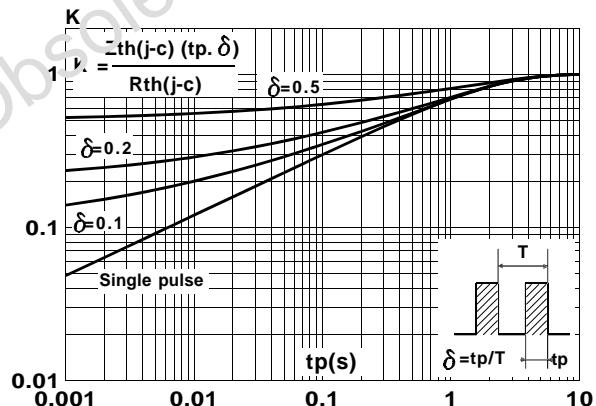
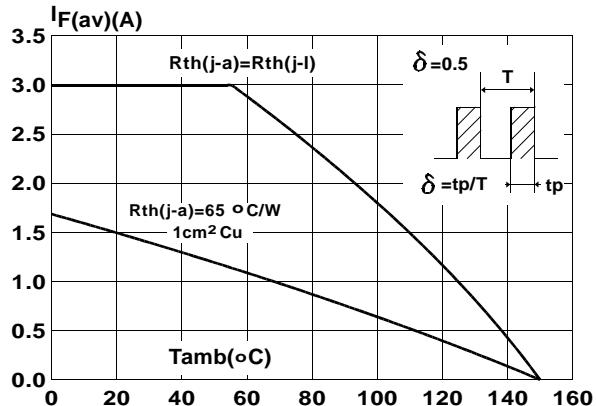


Fig.6 : Average current versus ambient temperature. (duty cycle : 0.5)



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Fig.7 : Recovery time versus dI_F/dt .

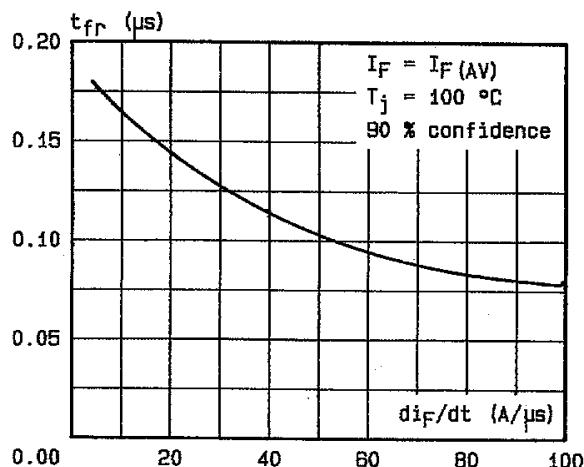


Fig.9 : Peak reverse current versus dI_F/dt .

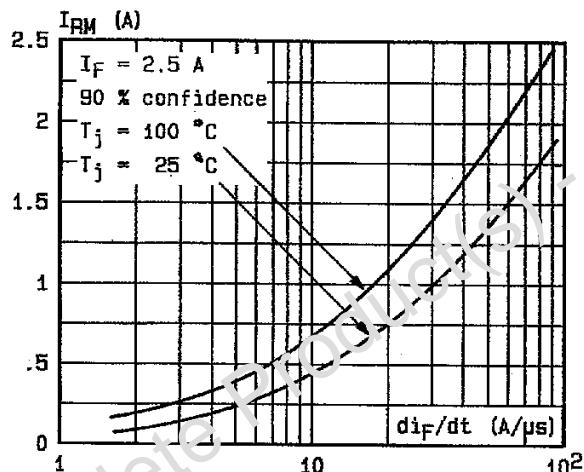


Fig.11 : Dynamic parameters versus junction temperature.

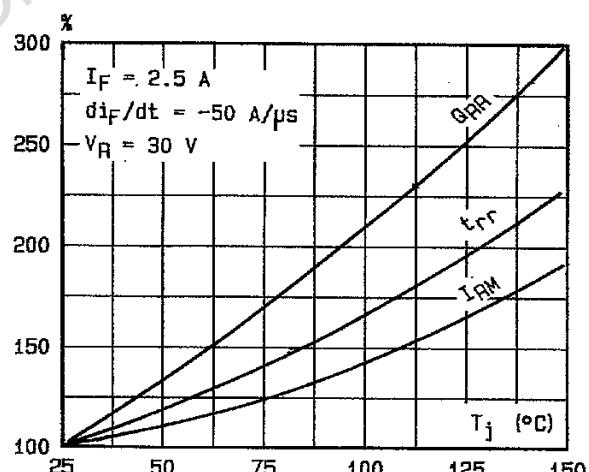


Fig.8 : Peak forward voltage versus dI_F/dt .

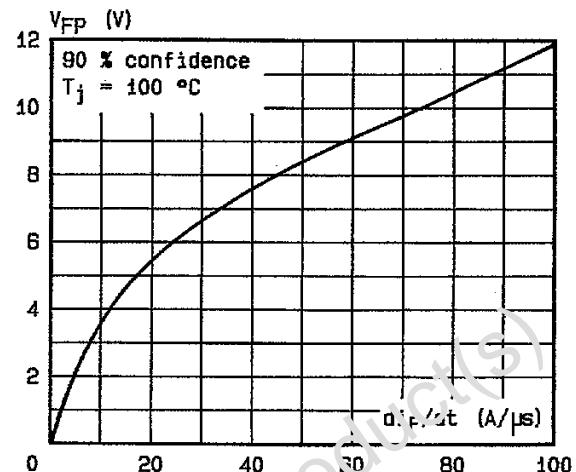


Fig.10 : Recovery charge versus dI_F/dt .
(typical values)

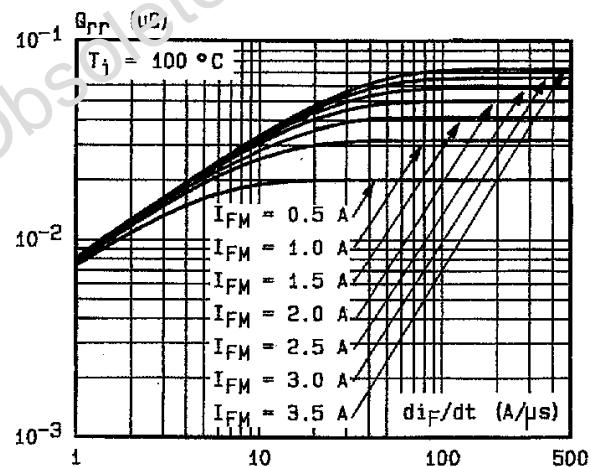
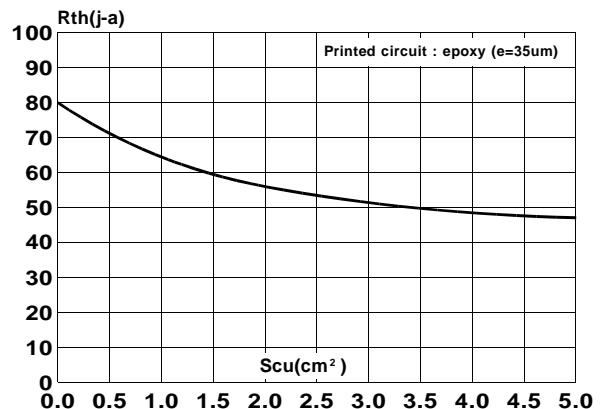


Fig.12 : Thermal resistance junction to ambient versus copper surface under each lead.



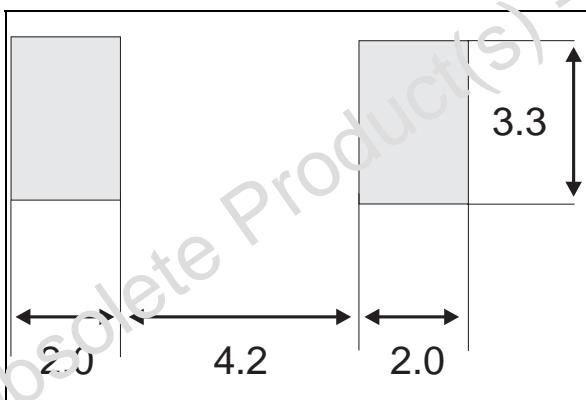
PACKAGE MECHANICAL DATA

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REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A1	1.90	2.45	0.075	0.096
A2	0.05	0.20	0.002	0.008
b	2.90	3.2	0.114	0.126
c	0.15	0.41	0.006	0.016
E	7.75	8.15	0.305	0.321
E1	6.60	7.15	0.260	0.281
E2	4.40	4.70	0.173	0.185
D	5.55	6.25	0.213	0.246
L	0.75	1.60	0.030	0.063

FOOTPRINT DIMENSIONS

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